

NAND-TYPE FLASH MEMORY DEVICES AND METHODS OF FABRICATING THE  
SAME

Abstract of the Disclosure

NAND-type flash memory devices and methods of fabricating the same are provided.

5      The NAND-type flash memory device includes a plurality of isolation layers running parallel with each other, which are formed at predetermined regions of a semiconductor substrate. This device also includes a string selection line pattern, a plurality of word line patterns and a ground selection line pattern which cross over the isolation layers and active regions between the isolation layers. Source regions are formed in the active regions adjacent to the ground selection

10     line patterns and opposite the string selection line pattern. The source regions and the isolation layers between the source regions are covered with a common source line running parallel with the ground selection line pattern.

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